

Features

- On-Chip Latches for Both DACs.
- +5V to +12V Operation .
- DACs Matched to 1%.
- Four Quadrant Multiplication.
- TTL/CMOS Compatibel from 5V to 12V.
- Full Temperature Operation.
- 8-bit Endpoint Linearity(+1/2 LSB)
- Microprocessor Compatible.

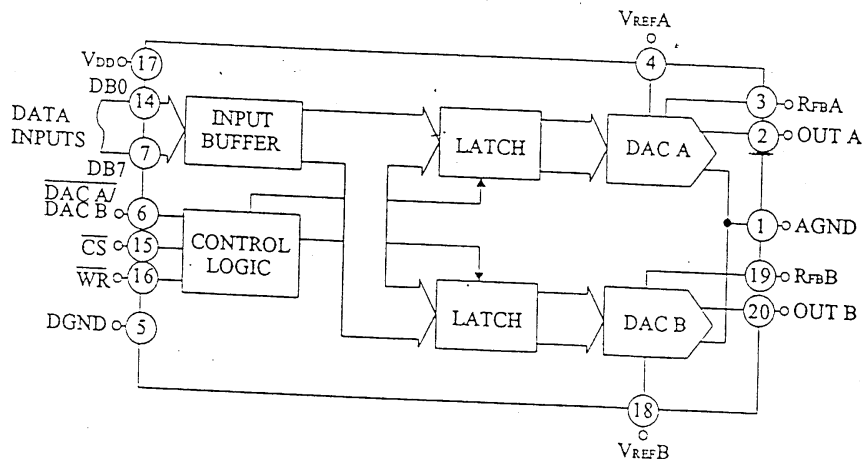
DESCRIPTION

ES52110 contains two & two 8-bit multiplying D/A converter in a single chip. This monolithic construction offers excellent DAC-to DAC matching and tracking. The ES 52110 consists of two R-2R resistor-ladder networks, two tracking span resistors, two data latches, one input buffer, and control logic circuit. Both DACs offer excellent four quadrant multiplication characteristics with a separated reference input and feedback resistor for each DAC.

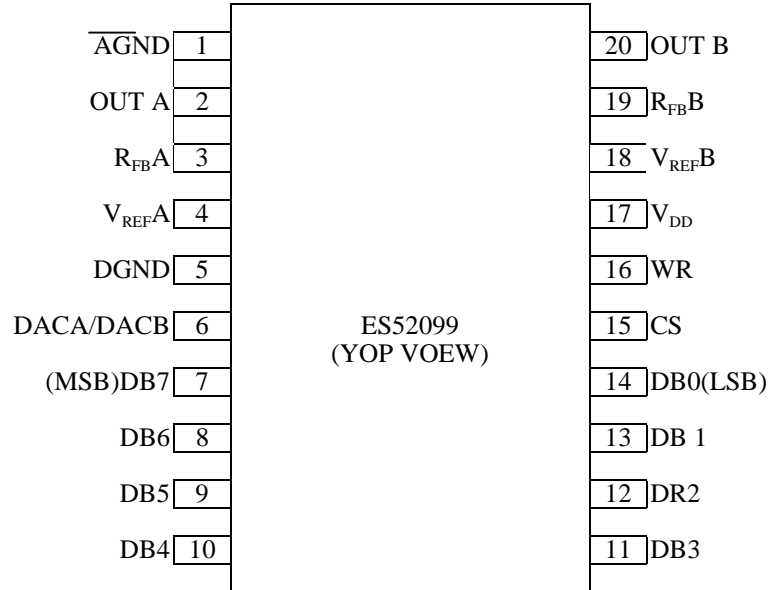
Applications

- Disk Drives
- Digital Gain/Attenuation Control
- Digitally-Controlled Filter Parameters

Block Diagram



PIN Assignment



Pin Description

Pin NUMBER.	NAME	TYPE	DESCRIPTION
1	AGND		The current from the digital input are switched between the DAC OUTPUT and AGND thus maintaining fixed current in each ladder leg. Independent of switch statc.
2	OUT A	O	Analog data is restored from D/A converter which the digital data is transferred into either of the two DAC.
20	OUT B	O	
3 19	R _{FB} A R _{FB} A		Internal feedback resistor
4 18	V _{REF} A R _{REF} B		The reference voltage for the R-2R ladder structure DAC.
5	DGND		
6	DAC A/D ACB	I	Both DAC latches share a common 8-bit input port. The control input DAC A/D ACB selects which DAC can accept data from the input port.
7-14	DB7-DB0	I	Data bus is TTL./CMOS compatible. Data is transferred into the either of two latches of DAC. DB0 is the least significant bit
15	CS	I	Input CS and WR control the operating mode of the selected DAC. When CS and WR are both low. The selected DAC is in the Write mode. The input data latches of the selected DAC are transparent and its analog output responds to activity on DB0-DB7
17	VDD		Power

FUNCTION DESCRIPTION :
Function Mode

The selected DAC latch retains the data which is present on DB0-DB7 just prior to \overline{CS} or \overline{WR} assuming a high state. Both analog outputs remain at the values corresponding to the data in their respective latches.

MODE SELECT TABLE

\overline{DAC} A/D ACB	\overline{CS}	\overline{WR}	DACA	DACB
L	L	L	WRITE	HOLD
H	L	L	HOLD	WRITE
X	H	X	HOLD	HOLD
X	X	H	HOLD	HOLD

L=Low State H=High State X=Don't Care

Circuit Description
***D/A Converter**

The ES 52110 contains two identical 8-bit multiplying D/A converters, DAC A and DAC B. Each DAC consists of a highly stable R-2R ladder and eight N-channel current steering switches. A simplified D/A circuit for DAC A is shown in Figure 1. An inverted R-2R ladder structure is used, that is, binary weighted currents are switched between the DAC output and AGND thus maintaining fixed currents in each ladder leg independent of switch state. There is normally closed switch in series with the internal feedback resistor (R_{FB}). This switch improves linearity performance over temperature and power supply rejection; however, when the circuit is not powered up, the switch assumes an open state.

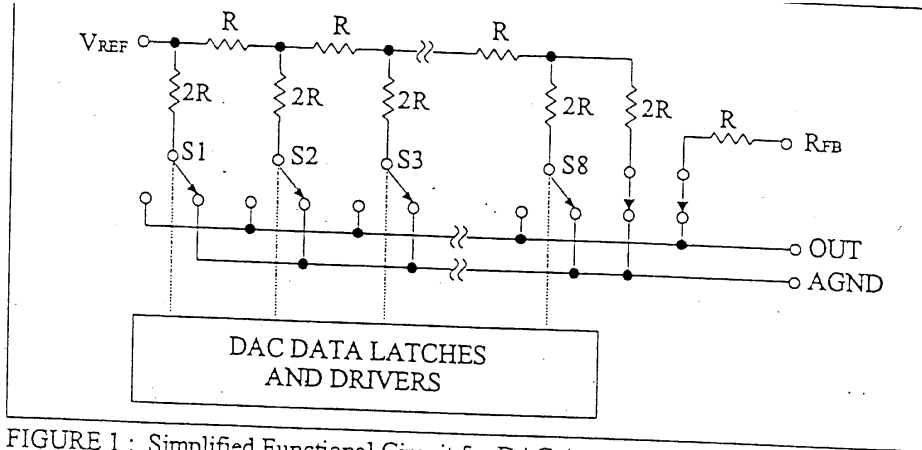


FIGURE 1 : Simplified Functional Circuit for DAC A or DAC B

*Equivalent Circuit

Figure 2 shows an approximate equivalent circuit for one of the ES 52110's D/A converters, in this case DAC A. A similar equivalent circuit can be drawn for DAC B. Note that AGND is common for both DAC A and DAC B. The current source I_{LKG} is composed of surface and junction leakages, as with most semiconductor devices, approximately doubles every 10°C . The resistor R_o as shown in Figure 2, is the equivalent output resistance of the device which varies with $11\text{k}\Omega$. C_{OUT} is the capacitance due to the N-channel switches and varies from about 50pF to 120pF , depending upon the digital input. $g(V_{REF,A,N})$ is the Thevenin equivalent voltage generator, due to the reference input voltage $V_{REF,A}$ and transfer function of the R-2R ladder.

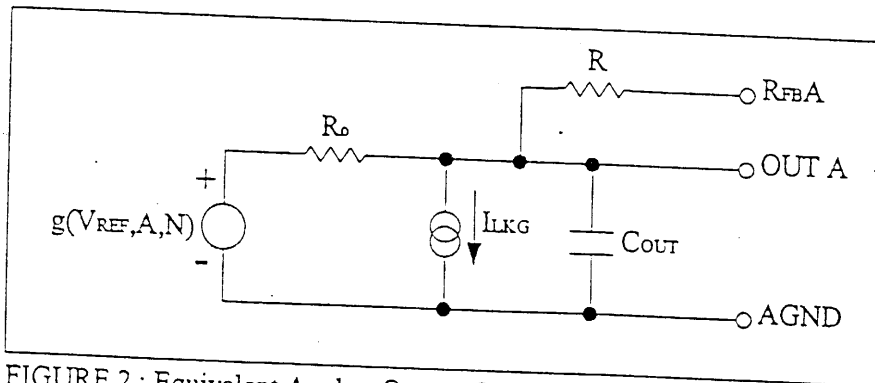


FIGURE 2 : Equivalent Analog Output Circuit of DAC A

ABSOLUTE MAXIMUM RATINGS

Parameter	Min	Type	Max	Unit
V_{DD} to AGND	0	—	+15	V
V_{DD} to AGND	0	—	+15	V
AGND to DGND	0	—	$V_{DD}+0.3$	V
Digital Input Vdtage to DGND	-0.3	—	$V_{DD}+0.3$	V
V_{PIN2} , V_{PIN20} to AGND	-0.3	—	V_{DD}	V
V_{REF} , V_{REFB} to AGND	-25	—	+20	V
$V_{RFB A}$, $V_{RFB B}$ to AGND	-25	—	+20	V
Operating Temperature Range	-55	—	+125	°C
Junction Temperature	—	—	+150	°C
Storage Temperature	-65	—	+150	°C
Lead Temperature	—	—	+300	°C

Notes:

1. Do not apply voltage higher than V_{DD} or less than GND potential on any terminal except V_{REF} .
2. The digital control inputs are Zener-Protected; however, permanent damage may occur on unprotected units from high-energy electrostatic fields. Keep units in conductive form at all times until ready for use.
3. Do not insert this device into powered sockets; remove power before insertion or removal.
4. Use proper antistatic handling procedures.
5. Stressed above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

Application Information

The most common application of this DAC is voltage output operation. Unipolar output operation provides a 0 to 10 volt output swing when connected, as shown in Figure 4. The maximum output voltage polarity is the inverse of the input reference voltage, since the op amp inverts the input currents. The transfer equation for unipolar operation is $V_{OUT} = -V_{IN} D/256$, where D is the decimal value of the data bit inputs DB0 THRU DB7 and V_{IN} is the reference input voltage. The transfer equation highlights another popular application of CMOS DAC's, The output voltage is the product of the reference voltage and the digital input code. The reference input voltage can be any value in the range of $\pm V_{CC}$ volts for both DC or AC signals. The circuit in Figure 4 performs two-quadrant multiplication. Table 1 provides example analog outputs for the given digital input codes.

For bipolar output operation connect the ES 52110 as shown in Figure 5. This circuit configuration provides an offset current, derived from the reference to enable the output op amp to swing in both polarities. The digital input coding becomes offset binary. Table 2 provides some example analog outputs for various digital inputs (D). The transfer equation for bipolar operation is $V_{OUT} = V_{IN} \times (D/128 - 1)$, where D is the decimal value of the data bit inputs DB0 thru DB7. This circuit provides full four-quadrant multiplication able to accept both polarities on all input as well as the circuit output.

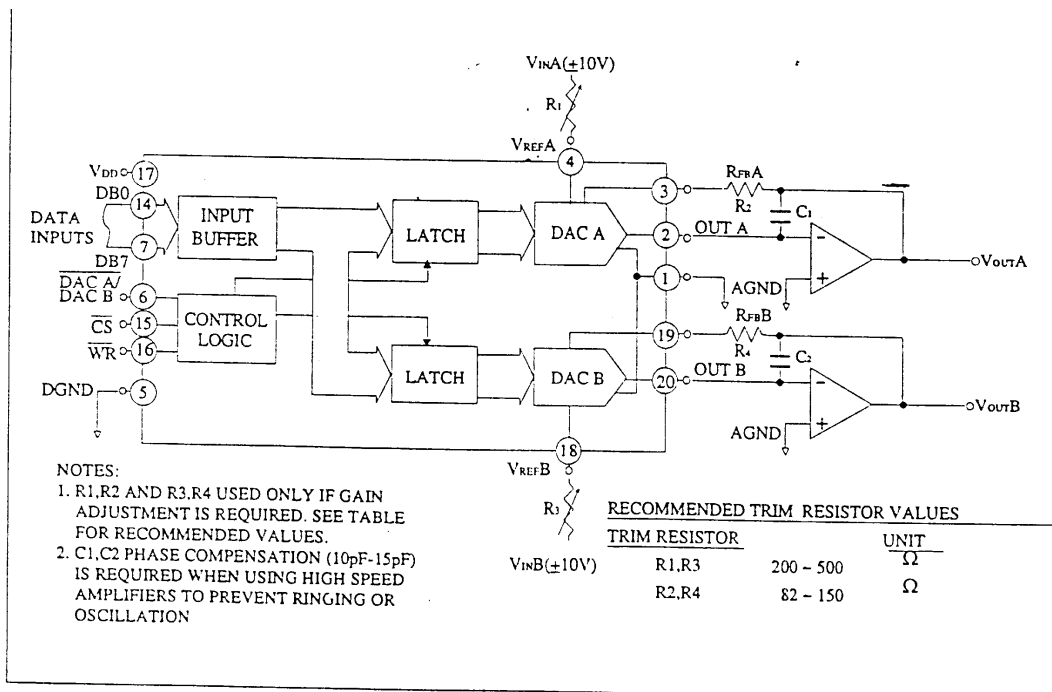


Figure 4. Dual DAC Unipolar Binary Operation (2 Quadrant Multiplication). See Table 1.

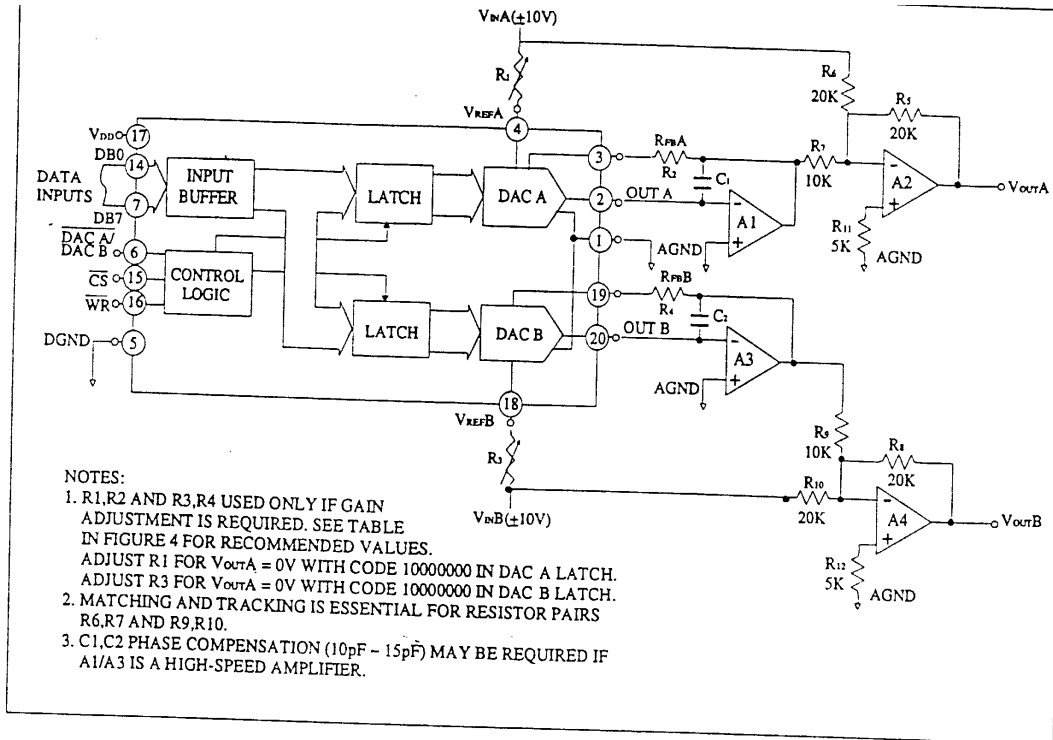


Figure 5. Dual DAC Bipolar Operation (4 Quadrant Multiplication). See Table 2.

DA LATCH CONTENTS MSB LSB	ANALOG OUTPUT (DAC A or DACB)
11111111	$-V_{IN}(255/256)$
1000001	$-V_{IN}(129/256)$
1000000	$-V_{IN}(128/256) = -V_{IN}/2$
01111111	$-V_{IN}(127/256)$
0000001	$-V_{IN}(1/256)$
0000000	$-V_{IN}(0/256) = 0$

Table 1. Unipolar Binary Code Table.
NOTE: $1 \text{ LSB} = (2^{-8})(V_{IN}) = (1/256)(V_{IN})$

DA LATCH CONTENTS MSB LSB	ANALOG OUTPUT (DAC A or DACB)
11111111	$+V_{IN}(127/128)$
1000001	$+V_{IN}(1/128)$
1000000	0
01111111	$+V_{IN}(1/128)$
0000001	$+V_{IN}(127/128)$
0000000	$+V_{IN}(128/128)$

Table 1. Unipolar Binary Code Table.
NOTE: $1 \text{ LSB} = (2^{-7})(V_{IN}) = (1/128)(V_{IN})$

ELECTRICAL CHARACTERISTICS
*** Operating Conditions:**

$V_{DD} = +5V \pm 5\%$; $V_{REFA} = V_{REFB} = +10V$; $I_{OUTA} = I_{OUTB} = 0V$; $T_A = \text{Full Temp. Range}$ specified under Absolute Maximum Rating, unless otherwise noted.

Static Accuracy

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Resolution	N		8	—	—	Bits
Relative Accuracy (Note 2)	INL		—	—	$\pm 1/2$	LSB
Differential Nonlinearity (Note 3)	INL		—	—	$\pm 1/2$	LSB
Full-Scale Gain Error (Note 4)	G_{FSE}	$T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	—	—	$\pm 1/2$	LSB
Input Resistance (V_{REFA} , V_{REFB}) (Note 6)	R_{IN}		8	—	15	$k\Omega$
Input Resistance Match (V_{REFA}/V_{REFB})	$\Delta R_{IN}/R_{IN}$		—	± 0.1	± 1	%

Digital Inputs
(Note 9)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Digital Input High (Note 8)	V_{INH}		2.4	—	—	V
Digital Input Low (Note 8)	V_{INL}		—	—	0.8	V
Input Current (Note 7)	V_{IN}	$T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	—	± 0.01	± 1 ± 10	μA
Input Capacitance (Note 10)	C_{IN}	DB0-DB7 WR, CS, DAV, A/DACB	—	—	10 15	pF

Switching Characteristics

(Note 10,11)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Chip Select to Write Set-Up To,e	t_{CS}		100	—	—	ns
Chip Select to Write Hold time	t_{CH}		10	—	—	ns
Chip Select to Write Hold time	t_{AS}		100	—	—	ns
Data Select to Write Set-Up time	t_{DS}		100	—	—	ns
Data Select to Write Hold time	t_{DH}		10	—	—	ns
Write Pulse Width	T_{WR}		90	—	—	ns

Power Supply

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Supply Current	I_{DD}	All Digital Input = V_{DE} or V_{NL}	—	—	1	mA
		All Digital Input = 0V or V_{DD} $T_A = +25^{\circ}C$ $T_A = \text{Full Temp. Range}$	— —	— —	0.5 1.0	mA

AC Performance Characteristic

Parameter	Symbol	Conditions	Min	Typ	Max	Units
DC Supply Rejection Ratio ($\Delta \text{gain} / \Delta V_{DD}$) (Note 13)	PSRR	$T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	— —	— —	0.02 0.04	%/%
Current Settling Time (Notes 10, 15, 16, 20)	ts	$T_A = \text{Full Temp. Range}$	— —	— —	350	ns
Digital Charge Injection (Note 17)	Q	$T_A = +25^\circ\text{C}$	—	100	—	nVs
Output Capacitance	C_{OUTA}	DAC Latches Loaded	—	—	25	pF
	C_{OUTA}	With 0000 0000	—	—	25	
	C_{OUTA}	DAC Latches Loaded With 0000 0000	— —	— —	60 60	pF
AC Feedthrough	FT_A	V_{REFA} to I_{axA} : $T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	— —	— —	-70 -65	dB
	FT_A	V_{REFA} to I_{axA} : $T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	— —	— —	-70 -65	dB
Channel-to-Channel Isolation (Note 19)	CCI_{BA}	V_{REFA} to I_{OUTB} : $V_{REFA} = +20\text{VP-P}$ Sinewave @ $f = 10\text{kHz}$ $V_{REFB} = 0\text{V}; T_A = 25^\circ\text{C}$	—	-80	—	dB
	CCI_{BA}	V_{REFA} to I_{OUTB} : $V_{REFA} = +20\text{VP-P}$ Sinewave @ $f = 10\text{kHz}$ $V_{REFB} = 0\text{V}; T_A = 25^\circ\text{C}$	—	-80	—	dB
Digital Crosstalk	Q	For Code Transition from 0000 0000 to 1111 1111 $T_A = +25^\circ\text{C}$	—	30	—	nVs
Harmonic Distortion	THD	$V_{DD} = 6\text{V}$ @ $f = 1\text{kHz}$ $T_A = +25^\circ\text{C}$	—	-85	—	dB

* Operating Conditions :

$V_{DD} = +12V \pm 5\%$; $V_{REFA} = V_{REFB} = +10V$; $I_{OUTA} = I_{OUTB} = 0V$; $T_A =$
 Full Temp. Range specified under Absolute Maximum Rating, unless
 otherwise noted.

Static Accuracy

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Resolution	N		8	—	—	Bits
Relative Accuracy (Note 2)	INL		—	—	$\pm 1/2$	LSB
Differential Nonlinearity (Note 3)	DNL		—	—	± 1	LSB
Full-Scale Gain Error (Note 4)	G_{FSE}	$T_A = +25^\circ C$ $T_A = \text{Full Temp. Range}$	—	± 0.5 ± 0.1	± 2 ± 3	LSB
Gain Temperature coefficient ($\Delta \text{gain} / \Delta \text{tempertme}$) (Note 4)	TCG_{FSE}		—	—	± 0.0035	$\% ^\circ C$
Output Leakage Current $I_{ATA}(\text{Pin 2}) I_{OUT}(\text{Pin 2})$ (Note 4)	I_{LKG}	$T_A = +25^\circ C$ $T_A = \text{Full Temp. Range}$	—	± 0.5 —	± 5 ± 200	nA
Input Resistance (V_{REFA}, V_{REFB}) (Note 6)	R_{IN}		8	—	15	$k\Omega$
Input Resistance Match (V_{REFA}, V_{REFB})	$\Delta R_{IN}/R_{IN}$		—	± 0.1	± 1	%

Digital Inputs

(Note 9)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Digital Input High (Note 8)	V_{INH}		3.4	—	—	V
Digital Input Low (Note 8)	V_{INL}		—	—	1.5	V
Input Current (Note 7)	I_{IN}	$T_A = +25^\circ C$ $T_A = \text{Full Temp. Range}$	—	± 0.01 —	± 1 ± 10	μA
Input Capacitance (Note 10)	C_{IN}	DB0-DB7 WR,CS,DAV A/DACB	—	—	10 15	pF

Switching Characteristics
 (Note 10, 11)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Chip Select to Write Set-Up Time	T_{CS}		60		—	ns
Chip Select to Write Hold Time	T_{CH}		10	—	—	ns
DAC Select to Write Set-Up Time	T_{AS}		60	—	—	ns
DAC Select to Write Hold Time	T_{AH}		10	—	—	ns
Data Select to Write Set-Up Time	T_{DS}		70	—	—	ns
Data Select to Write Hold Time	T_{DH}		10	—	—	ns
Write Pulse Width	T_{WR}		60	—	—	ns

Power Supply

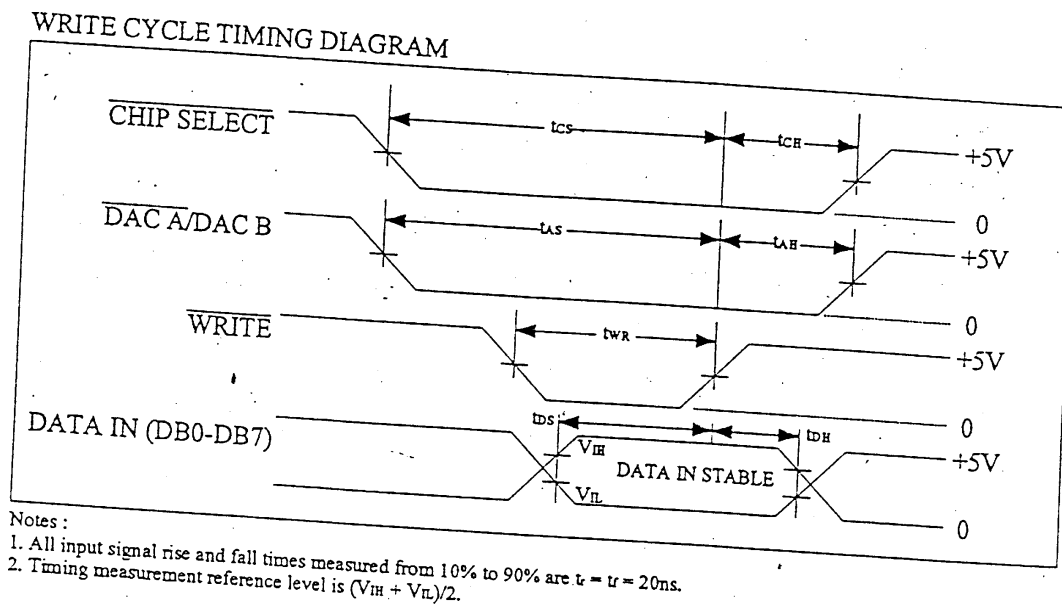
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Supply Current	I_{DD}	All Digital Input = V_{INH} or V_{INL}				
		$T_A = +25^\circ\text{C}$	—	—	6	
		$T_A = \text{Full Temp. Range}$	—	—	6.5	mA
		All Digital Input = 0V or V_{DD}				
		$T_A = +25^\circ\text{C}$	—	—	0.5	
		$T_A = \text{Full Temp. Range}$	—	—	1.0	mA

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
DC Supply Rejection Ratio ($\Delta \text{gain} / \Delta V_{DD}$) (Note 13)	PSRR	$T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	—	—	0.01 0.02	%/%
Current Settling Time (Note 10,15,16,20)	t_s	$T_A = \text{Full Temp. Range}$	—	—	250	ns
Digital Charge Injection (Note 17)	Q	$T_A = +25^\circ\text{C}$	—	160	—	nVs
Output Capacitance	C_{OUTA} C_{OUTA}	DAC Latches Loaded With 0000 0000	— —	— —	25 25	pF
	C_{OUTA} C_{OUTA}	DAC Latches Loaded With 0000 0000	— —	— —	60 60	pF
AC Feedthrough	FT_A	V_{REFA} to I_{AXA} : $T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	— —	— —	-70 -65	dB
	FT_B	V_{REFA} to I_{AXA} : $T_A = +25^\circ\text{C}$ $T_A = \text{Full Temp. Range}$	— —	— —	-70 -65	dB
Channel-to-Channel Isolation (Note 19)	CCI_{BA}	V_{REFA} to I_{OUTB} : $V_{REFA} = +20\text{VP-P}$ Sinewave @ $f = 10\text{kHz}$ $V_{REFB} = 0\text{V}; T_A = 25^\circ\text{C}$	—	-80	—	dB
	CCI_{AB}	V_{REFA} to I_{OUTB} : $V_{REFA} = +20\text{VP-P}$ Sinewave @ $f = 10\text{kHz}$ $V_{REFB} = 0\text{V}; T_A = 25^\circ\text{C}$	—	-80	—	dB
Digital Crosstalk	Q	For Code Transition from 0000 0000 to 1111 1111 $T_A = +25^\circ\text{C}$	—	50	—	nVs
Harmonic Distortion	THD	$V_{DD} = 6\text{V}$ @ $f = 1\text{kHz}$ $T_A = +25^\circ\text{C}$	—	-85	—	dB

Notes:

- Specifications apply to both DAC A and DAC B.
- This is an endpoint linearity specification.
- All grades guaranteed to be monotonic over the full operating the full operating temp. range.
- Measured using internal $R_{FB A}$ and $R_{FB B}$. Both DAC latches loaded with 1111 1111.
- DAC loaded with 0000 0000.
- Input resistance $T_C = 300 \text{ ppm}/^\circ\text{C}$.
- $V_{IN} = 0\text{V}$ or V_{DD} .
- For all data bits DB0-DB7, WR, CS, DAC A/DACB.
- Logic inputs are MOS gates. Typical input current($+25^\circ\text{C}$) is less than I_{nA} .
- Guaranteed and not tested.
- See timing diagram.
- These characteristics are for design guidance only and not subject to test.
- $\Delta V_{DD} = \pm 5\%$.
- From digital input to 90% of final analog-output current.
- $V_{REF A} = V_{REF B} = +10\text{V}; L_{OUT A}, I_{OUT B}$ load = 100Ω , $C_{EXT} = 13\text{Pf}$.
- WR, CS = 0V, DB0-DB7 = 0V to V_{DD} or V_{DD} to 0V.

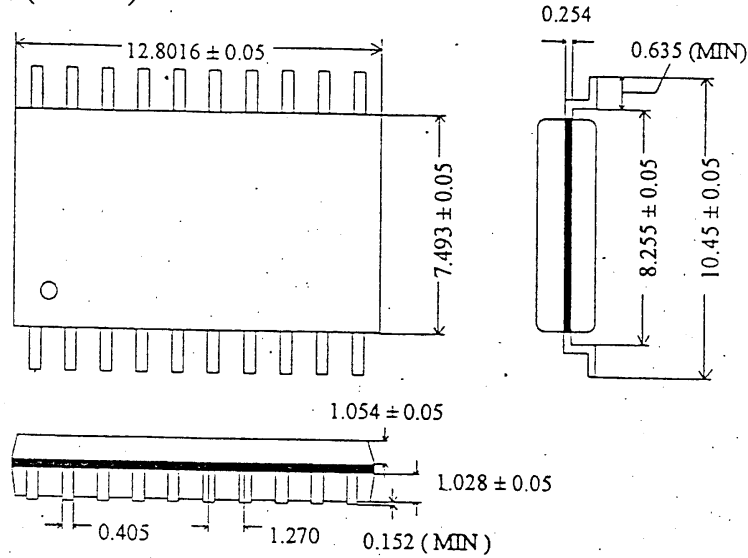
17. For code transition 0000 0000 to 1111 1111.
18. $V_{REFA}, V_{REFB} = 20V_{P-P}$ sinewave @ $f = 10kHz$.
19. Both DAC latches loaded with 1111 1111.
20. Extrapolated: $t_s(1/2LSB) = TPD + 6.2 \tau$, where τ = the measured first time constant of the final RC decay.

WRITE CYCLE TIMING DIAGRAM

Notes:

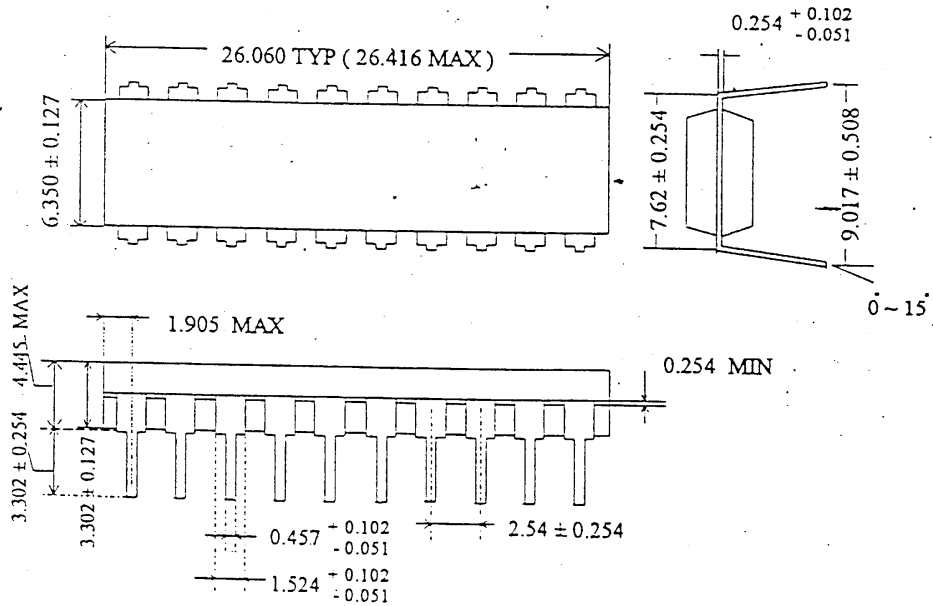
1. All input signal rise and fall times measured from 10% to 90% are $t_r = t_f = 20ns$.
2. Timing measurement reference level is $(V_{IH} + V_{IL})/2$.



ES52110S (SOP)



ES52110E (DIP)



unit : mm